

An Ultra-small, 17 mΩ, 2.5 A Load Switch

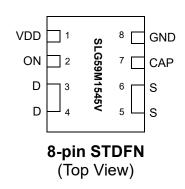
General Description

The SLG59M1545V is a 17 m Ω 2.5 A single-channel load switch that is able to switch 0.85 V to 5.5 V power rails. The product is packaged in an ultra-small 1.0 x 1.6 mm package.

Features

- 1.0 x 1.6 x 0.55 mm STDFN package (2 fused pins for drain and 2 fused pins for source)
- Logic level ON pin capable of supporting 0.85 V CMOS Logic
- · User selectable ramp rate with external capacitor
- 17 mΩ RDS_{ON} while supporting 2.5 A
- Two Over Current Protection Modes
- Short Circuit Current Limit
 - Active Current Limit
- Over Temperature Protection
- Pb-Free / Halogen-Free / RoHS compliant
- Operating Temperature: -20 °C to 70 °C
- Operating Voltage: 2.5 V to 5.5 V

Pin Configuration



Applications

- · Notebook Power Rail Switching
- Tablet Power Rail Switching
- Smartphone Power Rail Switching

2.5 A @ 17 mΩ D S C_{IN} VDD CLOAD +2.5 to 5.5 V Charge Pump Linear Ramp Control CAP CSLEW 4 nF Over Current and **Over Temperature** Protection ON **CMOS** Input

| Datasheet | |
|-----------|--|
| DataSheet | |

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Block Diagram

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Pin Description

| Pin # | Pin Name | Туре | Pin Description |
|-------|----------|--------|---|
| 1 | VDD | PWR | VDD supplies the power for the operation of the load switch and internal control circuitry. Bypass the VDD pin to GND with a 0.1 μF (or larger) capacitor. |
| 2 | ON | Input | A low-to-high transition on this pin initiates the operation of the SLG59M1545V's state machine. ON is a CMOS input with ON_V _{IL} < 0.3 V and ON_V _{IH} > 0.85 V thresholds. While there is an internal pull-down circuit to GND (~4 M Ω), connect this pin directly to a general-purpose output (GPO) of a microcontroller, an application processor, or a system controller. |
| 3, 4 | D | MOSFET | Drain terminal connection of the n-channel MOSFET (2 pins fused for D). Connect at least a low-ESR 0.1 μ F capacitor from this pin to ground. Capacitors used at D should be rated at 10 V or higher. |
| 5, 6 | S | MOSFET | Source terminal connection of the n-channel MOSFET (2 pins fused for S). Connect a low-ESR capacitor from this pin to ground and consult the Electrical Characteristics table for recommended C_{LOAD} range. Capacitors used at S should be rated at 10 V or higher. |
| 7 | CAP | Input | A low-ESR, stable dielectric, ceramic surface-mount capacitor connected from CAP pin to GND sets the V _S slew rate and overall turn-on time of the SLG59M1545V. For best performance C_{SLEW} value should be \geq 1.5 nF and voltage level should be rated at 10 V or higher. |
| 8 | GND | GND | Ground connection. Connect this pin to system analog or power ground plane. |

Ordering Information

| Part Number | Туре | Production Flow |
|---------------|--------------------------|-----------------------------|
| SLG59M1545V | STDFN 8L | Commercial, -20 °C to 70 °C |
| SLG59M1545VTR | STDFN 8L (Tape and Reel) | Commercial, -20 °C to 70 °C |

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SLG59M1545V

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Absolute Maximum Ratings

| Parameter | Description | Conditions | Min. | Тур. | Max. | Unit |
|--------------------------|-----------------------------------|--|------|------|-----------------|------|
| V _{DD} | Power Supply | | -0.3 | - | 7 | V |
| V _D to GND | Load Switch Input Voltage to GND | | -0.3 | - | V_{DD} | V |
| V_S to GND | Load Switch Output Voltage to GND | | -0.3 | | VD | V |
| ON and CAP to GND | ON and CAP Pin Voltages to GND | | -0.3 | | V _{DD} | V |
| Τ _S | Storage Temperature | | -65 | - | 150 | °C |
| ESD _{HBM} | ESD Protection | Human Body Model | 2000 | - | | V |
| ESD _{CDM} | ESD Protection | Charged Device Model | 500 | - | | V |
| θ_{JA} | Thermal Resistance | 1 x 1.6 mm, 8L STDFN; Determined using 1 in ² , 1 oz. copper pads under each D and S terminals and FR4 pcb material | | 72 | | °C/W |
| MOSFET IDS _{PK} | Peak Current from Drain to Source | For no more than 1 ms with 1% duty cycle | | | 3.5 | Α |

Note: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Electrical Characteristics

 T_A = -20 °C to 70 °C unless otherwise noted.

| Parameter | Description | Conditions | Min. | Тур. | Max. | Unit |
|-----------------------|------------------------------|---|--|----------|--------------------------------|------|
| V _{DD} | Power Supply Voltage | -20 °C to 70 °C | 2.5 | | 5.5 | V |
| 1 | Power Supply Current (DIN 1) | when OFF | | | 1 | μA |
| I _{DD} | Power Supply Current (PIN 1) | when ON, No load | | 75 | 100 | μA |
| PDS | ON Resistance | T _A = 25 °C, I _{DS} = 100 mA | | 17 | 19 | mΩ |
| RDS _{ON} | ON Resistance | T _A = 70 °C, I _{DS} = 100 mA | | 18.5 | 20 | mΩ |
| MOSFET IDS | Current from D to S | Continuous | | | 2.5 | Α |
| VD | Drain Voltage | | 0.85 | | V _{DD} | V |
| T _{ON_Delay} | ON Delay Time | 50% ON to V _S Ramp Start; C _{LOAD} = 10 μF, R _{LOAD} = 20 Ω | | 300 | 500 | μs |
| | | 50% ON to 90% V _S | Set by External C _{SLEW} ¹ | | | ms |
| T _{Total_ON} | Total Turn On Time | Example: C_{SLEW} = 4 nF, V _{DD} = V _D = 5 V, C _{LOAD} = 10 µF, R _{LOAD} = 20 Ω | | 1.50 | | ms |
| | | 10% $V_{\rm S}$ to 90% $V_{\rm S}$ | Set by | External | C _{SLEW} ¹ | V/ms |
| $V_{S(SR)}$ | Slew Rate | Example: C_{SLEW} = 4 nF, V _{DD} = V _D = 5 V, C _{LOAD} = 10 µF, R _{LOAD} = 20 Ω | | 3.4 | | V/ms |
| C _{LOAD} | Output Load Capacitance | C _{LOAD} connected from S to GND | | | 500 | μF |
| ON_V _{IH} | High Input Voltage on ON pin | | 0.85 | | V _{DD} | V |
| ON_V_{IL} | Low Input Voltage on ON pin | | -0.3 | 0 | 0.3 | V |

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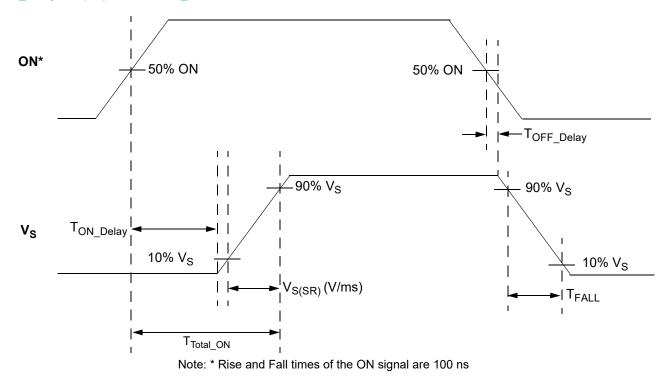
Electrical Characteristics (continued)

 T_A = -20 °C to 70 °C unless otherwise noted.

| Description | Conditions | Min. | Тур. | Max. | Unit |
|---|--|--|--|--|--|
| Active Current Limit, I _{ACL} | MOSFET will automatically limit current when V_S > 250 mV | | 3.7 | | A |
| Short Circuit Current Limit, I _{SCL} | MOSFET will automatically limit current when $\mathrm{V_S}$ < 250 mV | | 0.9 | | А |
| Thermal shutoff turn-on temperature | | | 125 | | °C |
| Thermal shutoff turn-off temperature | | | 100 | | °C |
| Thermal shutoff time | | | | 1 | ms |
| OFF Delay Time | 50% ON to V _S Fall Start; V _{DD} = V _D = 5 V; R _{LOAD} = 20 Ω , no C _{LOAD} | | 8 | | μs |
| V _S Fall Time | 90% V _S to 10% V _S , V _{DD} = V _D = 5 V R _{LOAD} = 20 Ω , no C _{LOAD} | | 3.8 | | μs |
| | Active Current Limit, I _{ACL} Short Circuit Current Limit, I _{SCL} Thermal shutoff turn-on temperature Thermal shutoff turn-off temperature Thermal shutoff time OFF Delay Time | Active Current Limit, I_{ACL} MOSFET will automatically limit current when $V_S > 250 \text{ mV}$ Short Circuit Current Limit, I_{SCL} MOSFET will automatically limit current when $V_S < 250 \text{ mV}$ Thermal shutoff turn-on temperatureThermal shutoff turn-off temperatureThermal shutoff turn-off temperature50% ON to V_S Fall Start; $V_{DD} = V_D = 5 \text{ V}$; $R_{LOAD} = 20 \Omega$, no C_{LOAD} 90% Valo 10% | Active Current Limit, I_{ACL} MOSFET will automatically limit current when $V_S > 250 \text{ mV}$ Short Circuit Current Limit, I_{SCL} MOSFET will automatically limit current when $V_S < 250 \text{ mV}$ Thermal shutoff turn-on temperatureThermal shutoff turn-off temperatureThermal shutoff timeOFF Delay Time50% ON to V_S Fall Start; $V_{DD} = V_D = 5 \text{ V}; \text{ R}_{LOAD} = 20 \Omega,$ $no C_{LOAD}$ V. Fall Time90% V_S to 10% V_S, $V_{DD} = V_D = 5 \text{ V}$ | Active Current Limit, I_{ACL} MOSFET will automatically limit current when $V_S > 250 \text{ mV}$ 3.7Short Circuit Current Limit, I_{SCL} MOSFET will automatically limit current when $V_S < 250 \text{ mV}$ 0.9Thermal shutoff turn-on temperature125Thermal shutoff turn-off temperature100Thermal shutoff timeOFF Delay Time 50% ON to V_S Fall Start; $V_{DD} = V_D = 5 \text{ V}; R_{LOAD} = 20 \Omega$, $no C_{LOAD}$ 8V. Fall Time 90% Vs to 10% Vs, Vpp = Vp = 5 V2.8 | Active Current Limit, I _{ACL} MOSFET will automatically limit current when $V_S > 250 \text{ mV}$ 3.7Short Circuit Current Limit, I _{SCL} MOSFET will automatically limit current when $V_S < 250 \text{ mV}$ 0.9Thermal shutoff turn-on temperature125100Thermal shutoff turn-off temperature1001Thermal shutoff turn-off temperature1001OFF Delay Time 50% ON to V_S Fall Start; $V_{DD} = V_D = 5 \text{ V}; \text{ R}_{LOAD} = 20 \Omega,$ $no C_{LOAD}$ 8V. Fall Time 90% V_S to 10% $V_S, V_{DD} = V_D = 5 \text{ V}$ 2.8 |

1. Refer to typical timing parameter vs. C_{SLEW} performance charts for additional information when available.

T_{ON_Delay}, V_{S(SR)}, and T_{Total_ON} Timing Details

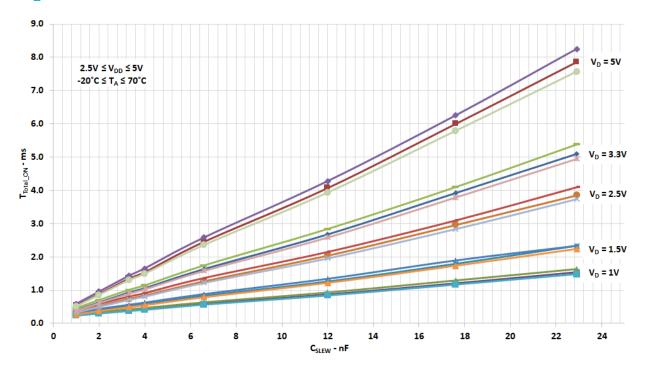




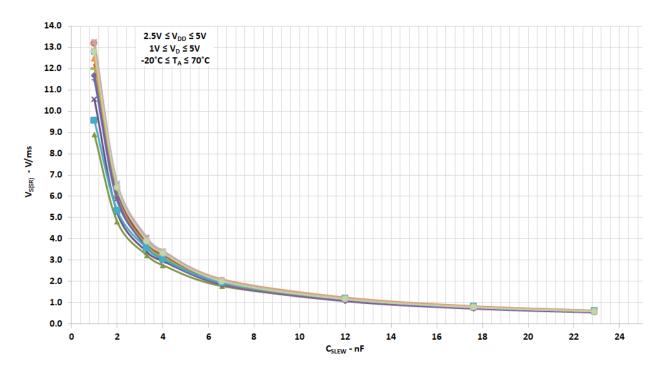
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Typical Performance Characteristics

$T_{Total_ON} \, vs \; C_{SLEW}, \, V_D, \, V_{DD}, \, and \; Temperature$



V_S Slew Rate vs. $C_{SLEW},\,V_{DD},\,and$ Temperature



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SLG59M1545V Power-Up/Power-Down Sequence Considerations

To ensure glitch-free power-up under all conditions, apply V_{DD} first, followed by V_D after V_{DD} exceeds 1.9 V. Then allow V_D to reach 90% of its max value before toggling the ON pin from Low-to-High. Likewise, power-down in reverse order.

If V_{DD} and V_D need to be powered up simultaneously, glitching can be minimized by having a suitable load capacitor. A 10 μ F C_{LOAD} will prevent glitches for rise times of V_{DD} and V_D higher than 2 ms.

If the ON pin is toggled HIGH before V_{DD} and V_D have reached their steady-state values, the load switch timing parameters may differ from datasheet specifications.

The slew rate of output V_S follows a linear ramp set by a capacitor connected to the CAP pin. A larger capacitor value at the CAP pin produces a slower ramp, reducing inrush current from capacitive loads.

SLG59M1545V Current Limiting Operation

The SLG59M1545V has two types of current limiting triggered by the output S pin voltage.

1. Standard Current Limiting Mode (with Thermal Shutdown Protection)

When the V_S voltage > 250 mV, the output current is initially limited to the Active Current Limit (I_{ACL}) specification listed in the Electrical Characteristics table. The ACL monitor's response time is very fast and is triggered within a few microseconds to sudden (transient) changes in load current. When a load current overload is detected, the ACL monitor increases the FET resistance to keep the current from exceeding the load switch's I_{ACL} threshold.

However, if a load-current overload condition persists where the die temperature rises because of the increased FET resistance, the load switch's internal Thermal Shutdown Protection circuit can be activated. If the die temperature exceeds the listed THER-M_{ON} specification, the FET is shut OFF completely, thereby allowing the die to cool. When the die cools to the listed THERM_{OFF} temperature threshold, the FET is allowed to turn back on. This process may repeat as long as the output current overload condition persists.

2. Short Circuit Current Limiting Mode (with Thermal Shutdown Protection)

When the V_S voltage < 250 mV (which is the case with a hard short, such as a solder bridge on the power rail), the load switch's internal Short-circuit Current Limit (SCL) monitor limits the FET current to approximately 900 mA (the I_{SCL} threshold). While the internal Thermal Shutdown Protection circuit remains enabled and since the I_{SCL} threshold is much lower than the I_{ACL} threshold, thermal shutdown protection may become activated only at higher ambient temperatures.

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|---|---|----|---|---|---|---|----|--|
| | a | ια | 9 | | C | C | L | |

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Power Dissipation

The junction temperature of the SLG59M1545V depends on different factors such as board layout, ambient temperature, and other environmental factors. The primary contributor to the increase in the junction temperature of the SLG59M1545V is the power dissipation of its power MOSFET. Its power dissipation and the junction temperature in nominal operating mode can be calculated using the following equations:

$$PD = RDS_{ON} \times I_{DS}^2$$

where: PD = Power dissipation, in Watts (W) RDS_{ON} = Power MOSFET ON resistance, in Ohms (Ω) I_{DS} = Output current, in Amps (A)

and

 $T_{.I} = PD \times \theta_{JA} + T_A$

where:

T_{.1} = Junction temperature, in Celsius degrees (°C) θ_{JA} = Package thermal resistance, in Celsius degrees per Watt (°C/W) T_A = Ambient temperature, in Celsius degrees (°C)

During active current-limit operation, the SLG59M1545V's power dissipation can be calculated by taking into account the voltage drop across the load switch (V_p - V_s) and the magnitude of the output current in active current-limit operation (I_{ACI}):

> $PD = (V_D - V_S) \times I_{ACL}$ or $PD = (V_D - (R_{LOAD} \times I_{ACL})) \times I_{ACL}$

where:

PD = Power dissipation, in Watts (W) V_D = Input Voltage, in Volts (V) R_{LOAD} = Load Resistance, in Ohms (Ω) I_{ACL} = Output limited current, in Amps (A) $V_{S} = R_{LOAD} \times I_{ACL}$

For more information on GreenFET load switch features, please visit our website and see App Note "AN-1068 GreenFET and High Voltage GreenFET Load Switch Basics".

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Layout Guidelines:

- 1. The VDD pin needs a 0.1 µF and 10 µF external capacitors to smooth pulses from the power supply. Locate these capacitors as close as possible to the SLG59M1545V's PIN1.
- 2. Since the D and S pins dissipate most of the heat generated during high-load current operation, it is highly recommended to make power traces as short, direct, and wide as possible. A good practice is to make power traces with absolute minimum widths of 15 mils (0.381 mm) per Ampere. A representative layout, shown in Figure 1, illustrates proper techniques for heat to transfer as efficiently as possible out of the device;
- To minimize the effects of parasitic trace inductance on normal operation, it is recommended to connect input C_{IN} and output C_{LOAD} low-ESR capacitors as close as possible to the SLG59M1545V's D and S pins;
- 4. The GND pin should be connected to system analog or power ground plane.
- 5. 2 oz. copper is recommended for high current operation.

SLG59M1545V Evaluation Board:

A GreenFET Evaluation Board for SLG59M1545V is designed according to the statements above and is illustrated on Figure 1. Please note that evaluation board has D_Sense and S_Sense pads. They cannot carry high currents and dedicated only for RDS_{ON} evaluation.

Please solder your SLG59M1545V here

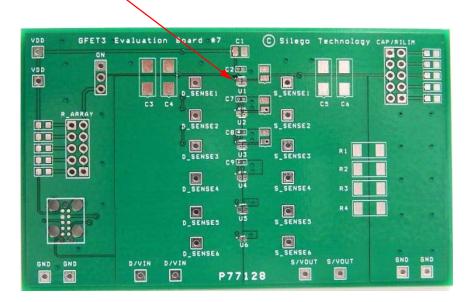


Figure 1. SLG59M1545V Evaluation Board.

| D . | ata | _ | | |
|------------|-----|-----|----|------------|
| | | en | | N P |
| | πα | 311 | 66 | τ. |



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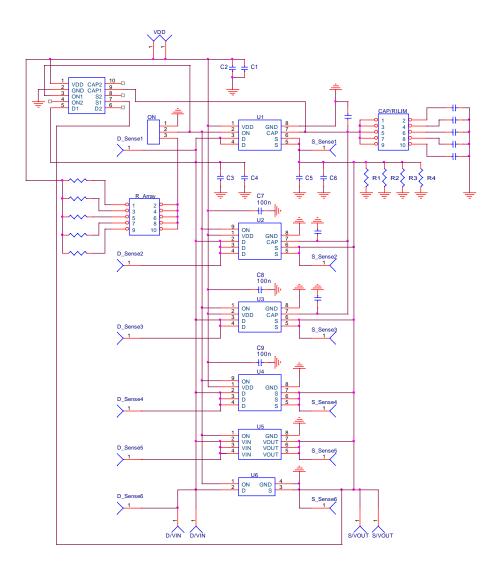


Figure 2. SLG59M1545V Evaluation Board Connection Circuit.

| Da | 4 - | | | |
|-------|------------|-----|----|--|
| 1 1 2 | | en | 00 | |
| 20 | | 311 | | |

Revision 1.03



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Basic Test Setup and Connections

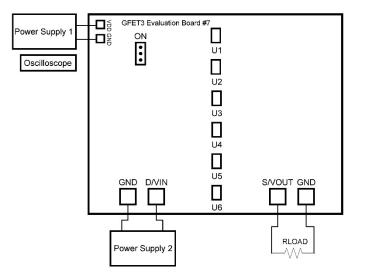


Figure 3. Typical connections for GreenFET Evaluation.

EVB Configuration

- 1. Connect oscilloscope probes to D/VIN, S/VOUT, ON, etc.;
- 2.Turn on Power Supply 1 and set desired V_{DD} from 2.5 V…5.5 V range;
- 3.Turn on Power Supply 2 and set desired V_{D} from 0.85 V...5.5 V range;
- 4.Toggle the ON signal High or Low to observe SLG59M1545V operation.



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Package Top Marking System Definition

| | ABC | Serial Number |
|------------------|-----|---------------|
| Pin 1 Identifier | 0 | |

ABC - 3 alphanumeric Part Serial Number where A, B, or C can be A-Z and 0-9

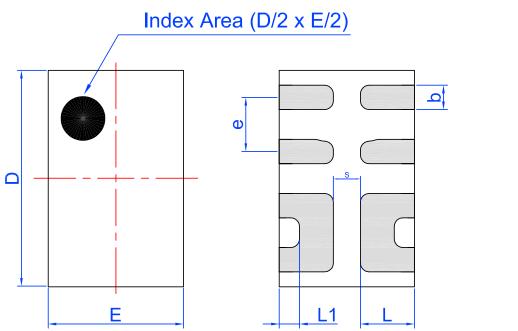
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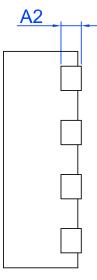


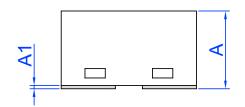
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Package Drawing and Dimensions









Unit: mm

| Symbol | Min | Nom. | Max | Symbol | Min | Nom. | Max |
|--------|-------|----------|-------|--------|------|---------|------|
| A | 0.50 | 0.55 | 0.60 | D | 1.55 | 1.60 | 1.65 |
| A1 | 0.005 | - | 0.060 | E | 0.95 | 1.00 | 1.05 |
| A2 | 0.10 | 0.15 | 0.20 | L | 0.35 | 0.40 | 0.45 |
| b | 0.13 | 0.18 | 0.23 | L1 | 0.10 | 0.15 | 0.20 |
| е | (|).40 BSC | , | S | (|).2 REF | |

| Datas | heet | |
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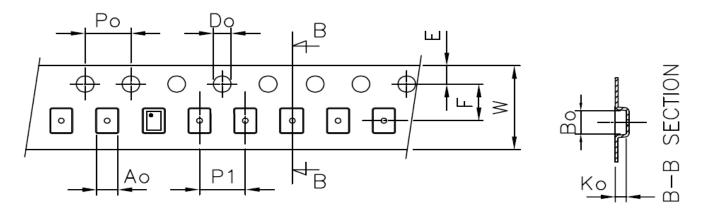
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Tape and Reel Specifications

| Package | # of | Nominal | Max | Units | Reel & | Leade | r (min) | Trailer | ' (min) | Таре | Part |
|---|------|----------------------|----------|---------|------------------|---------|----------------|---------|----------------|---------------|---------------|
| Туре | Pins | Package Size [mm] | per Reel | per Box | Hub Size [mm] | Pockets | Length [mm] | Pockets | Length [mm] | Width [mm] | Pitch [mm] |
| STDFN 8L 1x1.6mm 0.4P FC Green | | 1.0 x 1.6 x 0.55 | 3,000 | 3,000 | 178 / 60 | 100 | 400 | 100 | 400 | 8 | 4 |

Carrier Tape Drawing and Dimensions

| Package Type | Pocket BTM Length | Pocket BTM Width | Pocket Depth | Index Hole Pitch | Pocket Pitch | Index Hole Diameter | Index Hole to Tape Edge | Index Hole to Pocket Cen- ter | Tape Width |
|---|----------------------|---------------------|-----------------|---------------------|-----------------|------------------------|----------------------------|-------------------------------------|---------------|
| | A0 | B0 | K0 | P0 | P1 | D0 | E | F | w |
| STDFN 8L 1x1.6mm 0.4P FC Green | 1.12 | 1.72 | 0.7 | 4 | 4 | 1.55 | 1.75 | 3.5 | 8 |



Recommended Reflow Soldering Profile

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 0.88 mm³ (nominal). More information can be found at www.jedec.org.



An Ultra-small, 17 mΩ, 2.5 A Load Switch

Revision History

| Date | Version | Change |
|-----------|---------|---|
| 2/2/2022 | 1.03 | Updated Company name and logo |
| 11/7/2019 | 1.02 | Updated Style and Formatting Updated Abs. Max Table Added Layout Guidelines Fixed typos |
| 9/1/2016 | 1.01 | Updated Power Up/Down Sequencing Considerations Updated Current Limiting Description Updated text and parameter names for clarity |

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